ABSTRACT

In the inventive method for manufacturing a bipolar transistor having a polysilicon emitter, a collector region of a first conductivity type and, adjoining thereto, a basis region of a second conductivity type will be generated at first. At least one layer of an insulating material will now be applied, wherein the at least one layer is patterned such that at least one section of the basis region is exposed. Next, a layer of a polycrystalline semiconductor material of the first conductivity type, which is heavily doped with doping atoms, will be generated such that the exposed section is essentially covered. Now, a second layer of a highly conductive material on the layer of the polycrystalline semiconductor material will be generated in order to form an emitter double layer with the same. Thereupon, at least part of the doping atoms of the first conductivity type of the heavily doped polycrystalline semiconductor layer is caused to get into the basis region to generate an emitter region of the first conductivity type.

Fig. 2